March 1996



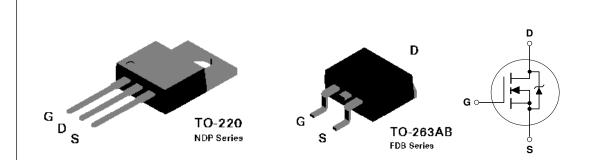
NDP7050 / NDB7050 N-Channel Enhancement Mode Field Effect Transistor

General Description

These N-Channel enhancement mode power field effect transistors are produced using Fairchild's proprietary, high cell density, DMOS technology. This very high density process is especially tailored to minimize on-state resistance, provide superior switching performance, and withstand high energy pulses in the avalanche and commutation modes. These devices are particularly suited for low voltage applications such as automotive, DC/DC converters, PWM motor controls, and other battery powered circuits where fast switching, low in-line power loss, and resistance to transients are needed.

Features

- 75A, 50V. $R_{DS(ON)} = 0.013\Omega @ V_{GS} = 10V.$
- Critical DC electrical parameters specified at elevated temperature.
- Rugged internal source-drain diode can eliminate the need for an external Zener diode transient suppressor.
- 175°C maximum junction temperature rating.
- High density cell design for extremely low R_{DS(ON)}.
- TO-220 and TO-263 (D²PAK) package for both through hole and surface mount applications.



Absolute Maximum Ratings T_c = 25°C unless otherwise noted

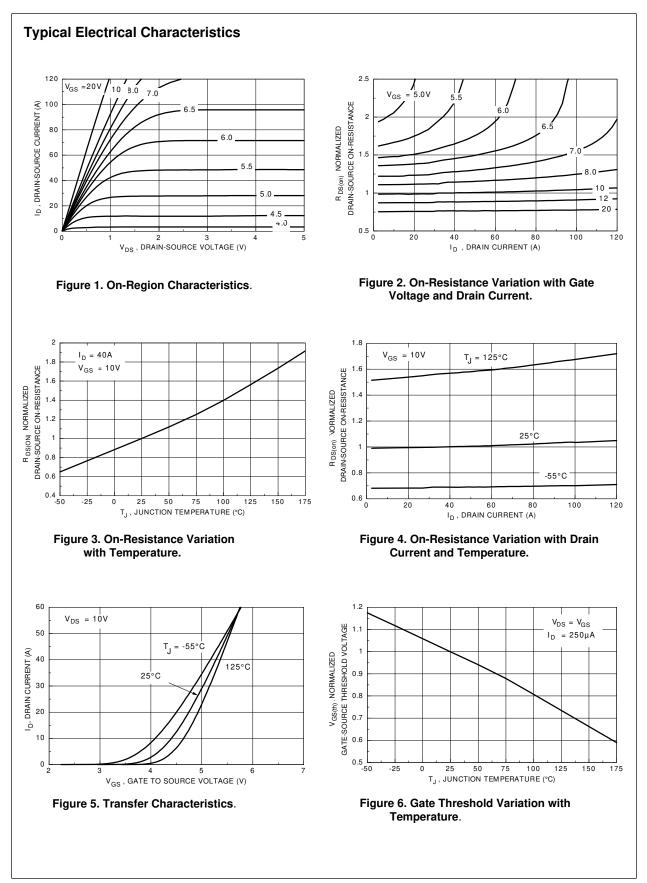
Symbol	Parameter	NDP7050	NDB7050	Units	
V _{DSS}	Drain-Source Voltage	50	50		
V_{DGR}	Drain-Gate Voltage ($R_{cs} \le 1 M\Omega$) 50			V	
V_{GSS}	Gate-Source Voltage - Continuous	± 20		V	
	- Nonrepetitive ($t_P < 50 \ \mu s$)	± 40			
I _D	Drain Current - Continuous	75		А	
	- Pulsed	225			
P _D	Maximum Power Dissipation @ $T_c = 25^{\circ}C$	150	W		
	Derate above 25°C	1	W/°C		
Tj,T _{stg}	Operating and Storage Temperature Range	-65 to 17	°C		
TL	Maximum lead temperature for soldering purposes, 1/8" from case for 5 seconds	275		°C	

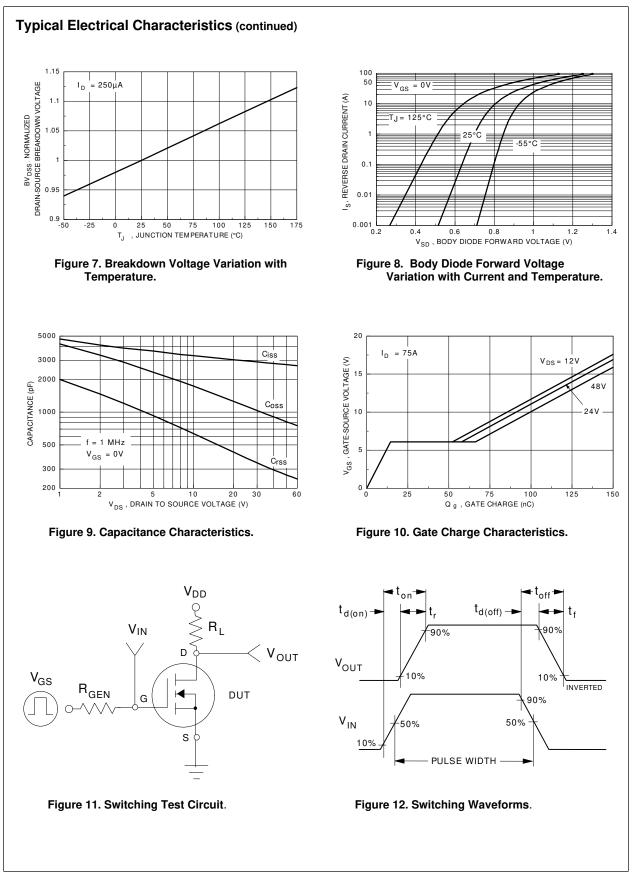
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Symbol	Parameter	Conditions		Min	Тур	Max	Units
DRAIN-S	OURCE AVALANCHE RATINGS (Note 1)						
W _{DSS}	Single Pulse Drain-Source Avalanche Energy	$V_{DD} = 25 \text{ V}, \text{ I}_{D} = 75 \text{ A}$				550	mJ
I _{AR}	Maximum Drain-Source Avalanche Curre	ent				75	Α
OFF CH/	ARACTERISTICS						
BV_{DSS}	Drain-Source Breakdown Voltage	$V_{\text{GS}}=0~V,~I_{\text{D}}=250~\mu\text{A}$		50			V
I _{DSS}	Zero Gate Voltage Drain Current	$V_{DS} = 50 \text{ V}, V_{GS} = 0 \text{ V}$	T _{.1} = 125°C			250 1	μA mA
IGSSF	Gate - Body Leakage, Forward	$V_{GS} = 20 \text{ V}, \text{ V}_{DS} = 0 \text{ V}$	1.5 .20 0			100	nA
I _{GSSR}	Gate - Body Leakage, Reverse	$V_{GS} = -20 \text{ V}, \text{ V}_{DS} = 0 \text{ V}$				-100	nA
ON CHAP	RACTERISTICS (Note 1)						
V _{GS(th)}	Gate Threshold Voltage	$V_{\rm DS} = V_{\rm GS}, I_{\rm D} = 250 \; \mu A$		2	2.8	4	V
co(iii)			T _J = 125°C	1.4	2.1	3.6	1
R _{DS(ON)}	Static Drain-Source On-Resistance	$V_{GS} = 10 \text{ V}, \text{ I}_{D} = 40 \text{ A}$ $T_{J} = 129 \text{ C}$			0.01	0.013	Ω
			T _J = 125°C		0.015	0.023	
I _{D(on)}	On-State Drain Current	$V_{GS} = 10 \text{ V}, V_{DS} = 10 \text{ V}$		75			Α
9 _{FS}	Forward Transconductance	$V_{\rm DS} = 10 \text{ V}, I_{\rm D} = 37.5 \text{ A}$		15	39		S
DYNAMIC	CHARACTERISTICS						
C _{iss}	Input Capacitance	$V_{DS} = 25 \text{ V}, V_{GS} = 0 \text{ V},$ f = 1.0 MHz			2960	3600	pF
C _{oss}	Output Capacitance				1130	1600	pF
C _{rss}	Reverse Transfer Capacitance				380	800	pF
SWITCHI	NG CHARACTERISTICS (Note 1)	-					
t _{D(on)}	Turn - On Delay Time	$V_{DD} = 30 \text{ V}, \text{ I}_{D} = 75 \text{ A},$ $V_{GS} = 10 \text{ V}, \text{ R}_{GEN} = 5 \Omega$			17	30	nS
ţ,	Turn - On Rise Time				128	400	nS
t _{D(off)}	Turn - Off Delay Time				54	80	nS
t _r	Turn - Off Fall Time				90	200	nS
Q _g	Total Gate Charge	$V_{DS} = 48 V,$ $I_{D} = 75 A, V_{GS} = 10 V$			100	115	nC
Q _{gs}	Gate-Source Charge	$I_{D} = 75 \text{ A}, V_{GS} = 10 \text{ V}$			14.5		nC
Q _{gd}	Gate-Drain Charge	7			51		nC

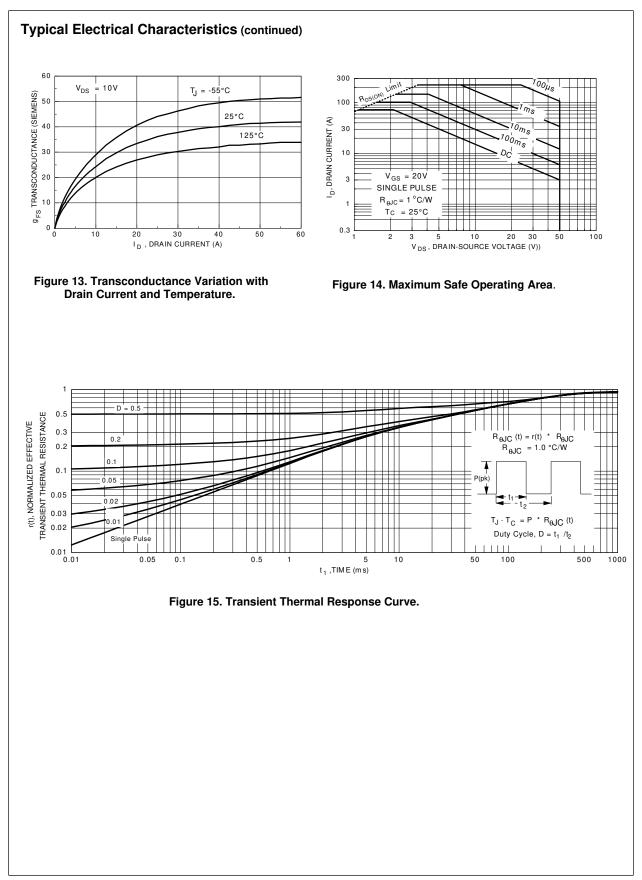
cal Characteristics (T _c = 25°C unless of	otherwise noted)					
Parameter	Conditions		Min	Тур	Max	Units
OURCE DIODE CHARACTERISTICS			•	•		
Maximum Continuos Drain-Source Diode Forward Current				75	Α	
Maximum Pulsed Drain-Source Diode Forward Current				225	Α	
Drain-Source Diode Forward Voltage	$V_{GS} = 0 \text{ V}, \text{ I}_{S} = 37.5 \text{ A} \text{ (Note 1)}$			0.9	1.3	V
		T _J = 125°C		0.84	1.2	
Reverse Recovery Time	$V_{GS} = 0 \text{ V}, \text{ I}_{\text{F}} = 75 \text{ A}, \text{ dI}_{\text{F}}/\text{dt} = 100 \text{ A}/\mu\text{s}$			80	150	ns
Reverse Recovery Current			2	4.8	10	Α
L CHARACTERISTICS			•	•		
Thermal Resistance, Junction-to-Case					1	°C/W
Thermal Resistance, Junction-to-Ambient				62.5	°C/W	
	Parameter DURCE DIODE CHARACTERISTICS Maximum Continuos Drain-Source Diode Maximum Pulsed Drain-Source Diode For Drain-Source Diode Forward Voltage Reverse Recovery Time Reverse Recovery Current L CHARACTERISTICS Thermal Resistance, Junction-to-Case	DURCE DIODE CHARACTERISTICS Maximum Continuos Drain-Source Diode Forward Current Maximum Pulsed Drain-Source Diode Forward Current Drain-Source Diode Forward Voltage V _{GS} = 0 V, I _S = 37.5 A (Note 1) Reverse Recovery Time Reverse Recovery Current L CHARACTERISTICS Thermal Resistance, Junction-to-Case	Parameter Conditions DURCE DIODE CHARACTERISTICS Maximum Continuos Drain-Source Diode Forward Current Maximum Pulsed Drain-Source Diode Forward Current Drain-Source Diode Forward Voltage V _{GS} = 0 V, I _S = 37.5 A (Note 1) T _J = 125°C Reverse Recovery Time V _{GS} = 0 V, I _F = 75 A, dI _F /dt = 100 A/µs Reverse Recovery Current CHARACTERISTICS Thermal Resistance, Junction-to-Case Thermal Resistance, Junction-to-Case	Parameter Conditions Min DURCE DIODE CHARACTERISTICS Maximum Continuos Drain-Source Diode Forward Current Image: Condition to the forward Current Image: Condition to the forward Current Maximum Pulsed Drain-Source Diode Forward Current Image: Condition to the forward Current Image: Condition to the forward Current Image: Condition to the forward Current Drain-Source Diode Forward Voltage $V_{GS} = 0 V$, $I_S = 37.5 A$ (Note 1) $T_J = 125^{\circ}C$ Image: Condition to the forward Voltage Image: Condit Image: Condition to the forward Voltage	ParameterConditionsMinTypDURCE DIODE CHARACTERISTICSMaximum Continuos Drain-Source Diode Forward CurrentImage: CurrentImage: CurrentMaximum Pulsed Drain-Source Diode Forward CurrentImage: CurrentImage: CurrentDrain-Source Diode Forward Voltage $V_{GS} = 0 V$, $I_S = 37.5 A$ (Note 1) $T_J = 125^{\circ}C$ 0.9 Image: Current Problem CurrentImage: CurrentImage: Current 0.9 $T_J = 125^{\circ}C$ 0.84 Reverse Recovery Time $V_{GS} = 0 V$, $I_F = 75 A$, $dI_F/dt = 100 A/\mu s$ 80 80 Reverse Recovery CurrentImage: CurrentImage: Current 2 4.8 L CHARACTERISTICSThermal Resistance, Junction-to-CaseImage: CurrentImage: CurrentImage: Current	ParameterConditionsMinTypMaxDURCE DIODE CHARACTERISTICSMaximum Continuos Drain-Source Diode Forward Current75Maximum Pulsed Drain-Source Diode Forward Current225Drain-Source Diode Forward Voltage $V_{GS} = 0 V$, $I_S = 37.5 A$ (Note 1) $T_J = 125^{\circ}C$ 0.84Reverse Recovery Time $V_{GS} = 0 V$, $I_F = 75 A$, $dI_F/dt = 100 A/\mu s$ 80150Reverse Recovery Current24.810L CHARACTERISTICSThermal Resistance, Junction-to-Case1

Note: 1. Pulse Test: Pulse Width \leq 300 µs, Duty Cycle \leq 2.0%.

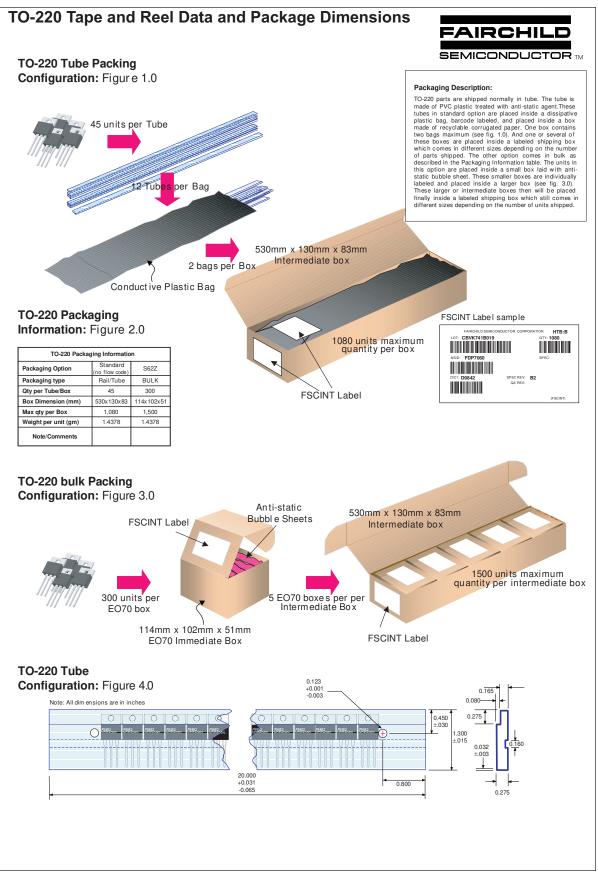




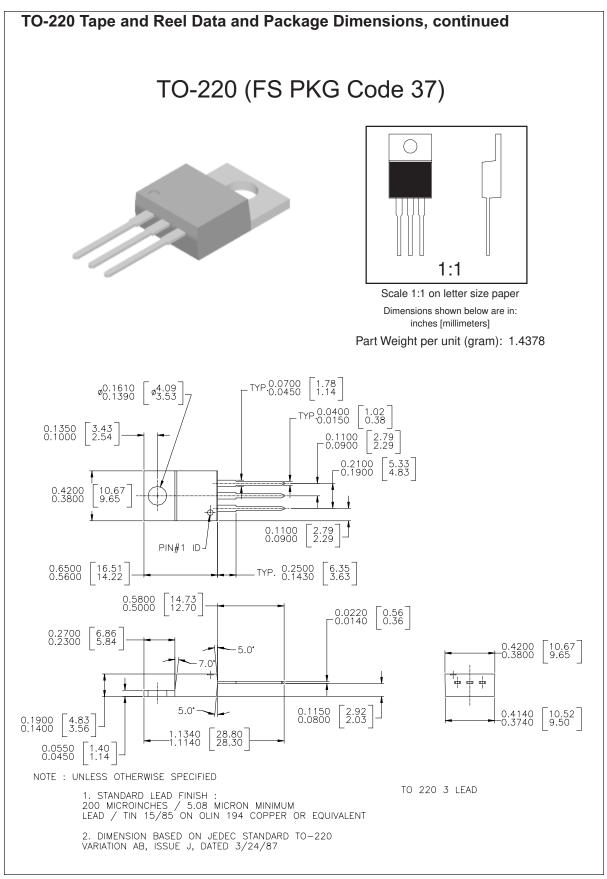
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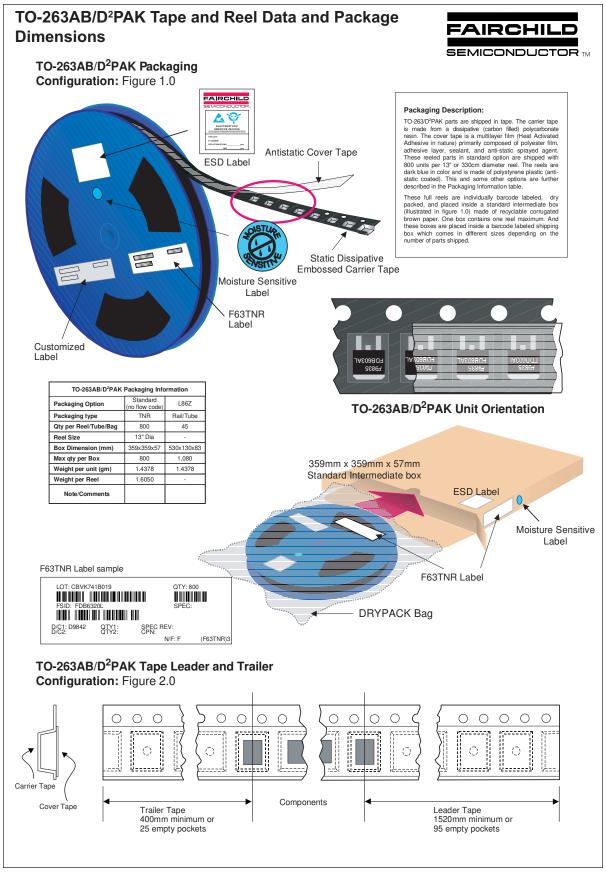
NDP7050.SAM Rev. D



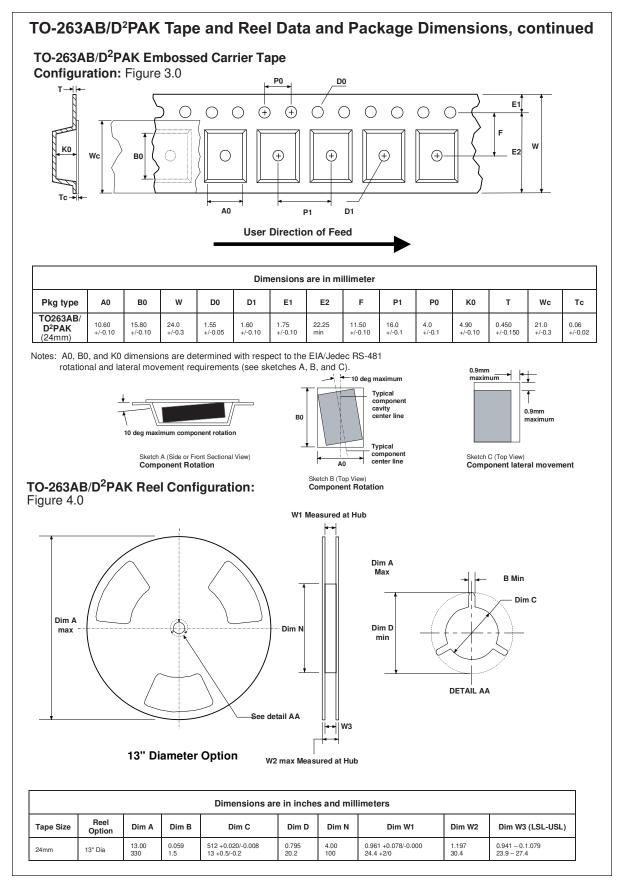
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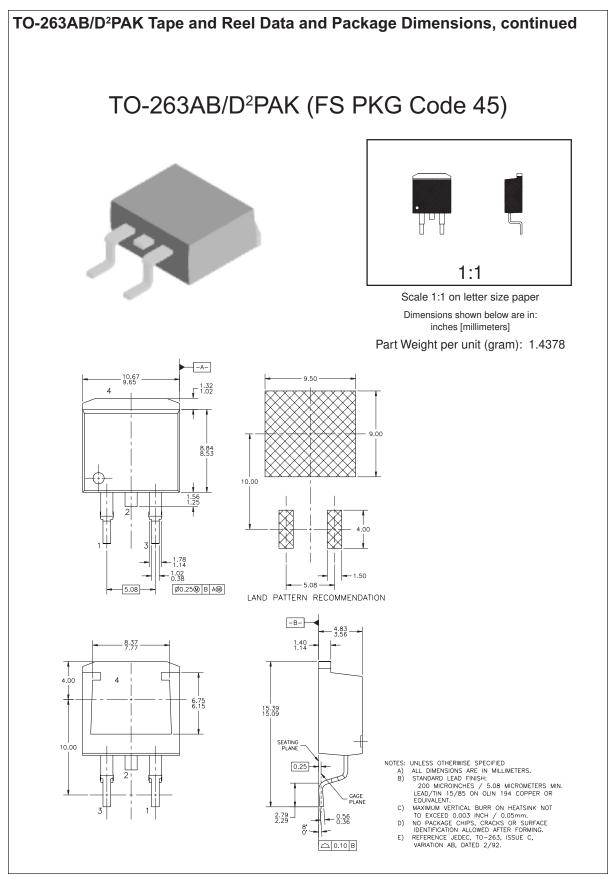


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